

SN65EPT22 3.3 V Dual LVTT/LVCmos to Differential LVPECL Buffer

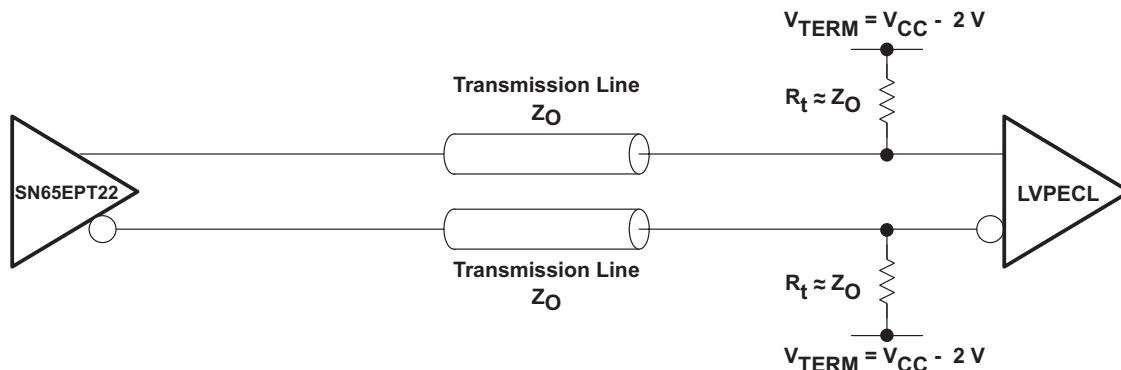
1 Features

- Dual 3.3V LVTT/LVCmos to Differential LVPECL Buffer
- Operating Range
 - LVPECL V_{CC} = 3.0 V to 3.6 V With $GND = 0$ V
- Support for Clock Frequencies to 2.0 GHz (typ)
- 420 ps Typical Propagation Delay
- Deterministic HIGH Output Value for Open Input Conditions
- Built-in Temperature Compensation
- Drop in Compatible to MC100ELT23
- PNP Single Ended Inputs for Minimal Loading

2 Applications

- Data and Clock Transmission Over Backplane
- Signaling Level Conversion

4 Simplified Schematic



3 Description

The SN65EPT22 is a low power dual LVTT/LVCmos to Differential LVPECL translator device. The device includes circuitry to maintain known logic HIGH level when inputs are in open condition. The SN65EPT22 is housed in an industry standard SOIC-8 package and is also available in TSSOP-8 package option.

Device Information⁽¹⁾

PART NUMBER	PACKAGE	BODY SIZE (NOM)
SN65EPT22	SOIC (8)	4.90mm x 3.91mm
	VSSOP (8)	3.00mm x 3.00mm

(1) For all available packages, see the orderable addendum at the end of the datasheet.



An IMPORTANT NOTICE at the end of this data sheet addresses availability, warranty, changes, use in safety-critical applications, intellectual property matters and other important disclaimers. PRODUCTION DATA.

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5 Revision History

NOTE: Page numbers for previous revisions may differ from page numbers in the current version.

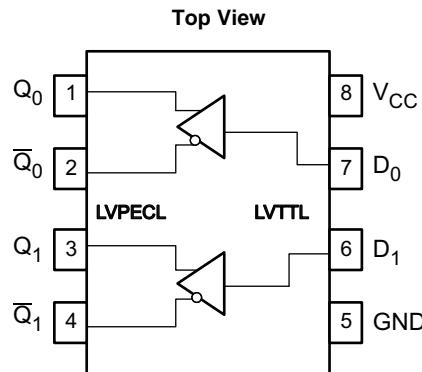
Changes from Revision A (November 2010) to Revision B

		Page
•	Deleted the Ordering Information table	1
•	Added the Device Information table	1
•	Added the Simplified Schematic	1
•	Added the Handling Ratings	3
•	Added the Device and Documentation Support and Mechanical, Packaging, and Orderable Information	8

Changes from Original (November 2010) to Revision A

		Page
•	Changed SN65EPT22 to EPT22 (2 places) in Ordering Information Table under Part Marking column	1

6 Pin Configuration and Functions



Pin Functions

PIN	FUNCTION
D ₀ , D ₁	LVTTL data inputs
Q ₀ , \overline{Q}_0 , Q ₁ , \overline{Q}_1	LVPECL outputs
V _{CC}	Positive supply
GND	Ground

7 Specifications

7.1 Absolute Maximum Ratings⁽¹⁾

PARAMETER	CONDITION	MIN	MAX	UNIT
Absolute supply voltage, V _{CC}			6	V
Absolute input voltage, VI	GND = 0 and VI \leq V _{CC}	0	6	V
Supply voltage LVPEL			3.3	V
Output current	Continuous		50	mA
	Surge		100	
Operating temperature range		-40	85	°C

(1) Stresses beyond those listed under *absolute maximum ratings* may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under *recommended operating conditions* is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

7.2 Handling Ratings

T _{stg}	Storage temperature range		MIN	MAX	UNIT
T _{stg}	Storage temperature range		-65	150	°C
V _(ESD)	Electrostatic discharge	Human body model (HBM), per ANSI/ESDA/JEDEC JS-001, all pins ⁽¹⁾	-4	4	kV
		Charged device model (CDM), per JEDEC specification JESD22-C101, all pins ⁽²⁾	-2	2	

(1) JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.
(2) JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.

7.3 Power Dissipation Ratings

PACKAGE	CIRCUIT BOARD MODEL	POWER RATING $T_A < 25^\circ\text{C}$ (mW)	THERMAL RESISTANCE, JUNCTION TO AMBIENT NO AIRFLOW	DERATING FACTOR $T_A > 25^\circ\text{C}$ (mW/ $^\circ\text{C}$)	POWER RATING $T_A = 85^\circ\text{C}$ (mW)
D	Low-K	719	139	7	288
	High-K	840	119	8	336
DGK	Low-K	469	213	5	188
	High-K	527	189	5	211

7.4 Thermal Information

THERMAL METRIC ⁽¹⁾	D	DGK	UNIT
	8 PINS	8 PINS	
$R_{\theta JB}$ Junction-to-board thermal resistance	79	120	$^\circ\text{C}/\text{W}$
$R_{\theta JC}$ Junction-to-case thermal resistance	98	74	

(1) For more information about traditional and new thermal metrics, see the *IC Package Thermal Metrics* application report, [SPRA953](#).

7.5 Key Attributes

CHARACTERISTICS	VALUE
Moisture sensitivity level	Lead free package
	SOIC-8
	VSSOP-8
Flammability rating (Oxygen Index: 28 to 34)	UL 94 V-0 at 0.125 in
Meets or exceeds JEDEC Spec EIA/JESD78 latchup test	

7.6 TTL Input DC Characteristics⁽¹⁾

($V_{CC} = 3.3$ V, $GND = 0$, $T_A = -40^\circ\text{C}$ to 85°C)

CHARACTERISTIC	CONDITION	MIN	TYP	MAX	UNIT
I_{IH} Input HIGH current	$V_{IN} = 2.7$ V			20	μA
I_{IHH} Input HIGH current max	$V_{IN} = V_{CC}$			100	μA
I_{IL} Input LOW current	$V_{IN} = 0.5$ V			-0.6	mA
V_{IK} Input clamp voltage	$I_{IN} = -18$ mA			-1	V
V_{IH} Input high voltage		2.0			V
V_{IL} Input low voltage			0.8		V

(1) Device will meet the specifications after thermal balance has been established when mounted in a socket or printed circuit board with maintained transverse airflow greater than 500 lfpm. Electrical parameters are assured only over the declared operating temperature range. Functional operation of the device exceeding these conditions is not implied. Device specification limit values are applied individually under normal operating conditions and not valid simultaneously.

7.7 PECL Output DC Characteristics⁽¹⁾

($V_{CC} = 3.3$ V; GND = 0.0V)⁽²⁾

CHARACTERISTIC		-40°C			25°C			85°C			UNIT
		MIN	TYP	MAX	MIN	TYP	MAX	MIN	TYP	MAX	
I _{CC}	Power supply current		39	45		42	47		45	50	mA
V _{OH}	Output HIGH voltage ⁽³⁾	2155	2224	2405	2155	2224	2405	2155	2224	2405	mV
V _{OL}	Output LOW voltage ⁽³⁾	1355	1441	1605	1355	1438	1605	1355	1435	1605	mV

(1) Device will meet the specifications after thermal balance has been established when mounted in a socket or printed circuit board with maintained transverse airflow greater than 500 lfm. Electrical parameters are assured only over the declared operating temperature range. Functional operation of the device exceeding these conditions is not implied. Device specification limit values are applied individually under normal operating conditions and not valid simultaneously.

(2) Output parameters vary 1:1 with V_{CC}

(3) All loading with 50Ω to V_{CC} – 2.0V

7.8 AC Characteristics⁽¹⁾

($V_{CC} = 3.0$ V to 3.6 V; GND = 0 V)⁽²⁾

CHARACTERISTIC		-40°C			25°C			85°C			UNIT
		MIN	TYP	MAX	MIN	TYP	MAX	MIN	TYP	MAX	
f _{MAX}	Max switching frequency ⁽³⁾ , see Figure 5		2.1			2.0			2.0		GHz
t _{PLH} / t _{PHL}	Propagation delay to differential output	230		550	230		550	230		550	ps
t _{SKEW}	Within device skew ⁽⁴⁾		25	50		25	50		25	50	ps
	Device to device skew ⁽⁵⁾		100	200		100	200		100	200	ps
t _{JITTER}	Random clock jitter (RMS)		0.2	0.8		0.2	0.8		0.2	0.8	ps
t _r / t _f	Output rise/fall times (20%–80%)	150		300	150		300	150		300	ps

(1) Device will meet the specifications after thermal equilibrium has been established when mounted in a test socket or printed circuit board with maintained transverse airflow greater than 500 lfm. Electrical parameters are assured only over the declared operating temperature range. Functional operation of the device exceeding these conditions is not implied. Device specification limit values are applied individually under normal operating conditions and not valid simultaneously.

(2) Measured using a 2.4 V source, 50% duty cycle clock source. All loading with 50Ω to V_{CC} – 2.0 V.

(3) Maximum switching frequency measured at output amplitude of 300 mV_{PP}.

(4) Skew is measured between outputs under identical transitions and conditions on any one device.

(5) Device-to-Device Skew for identical transitions at identical V_{CC} levels.

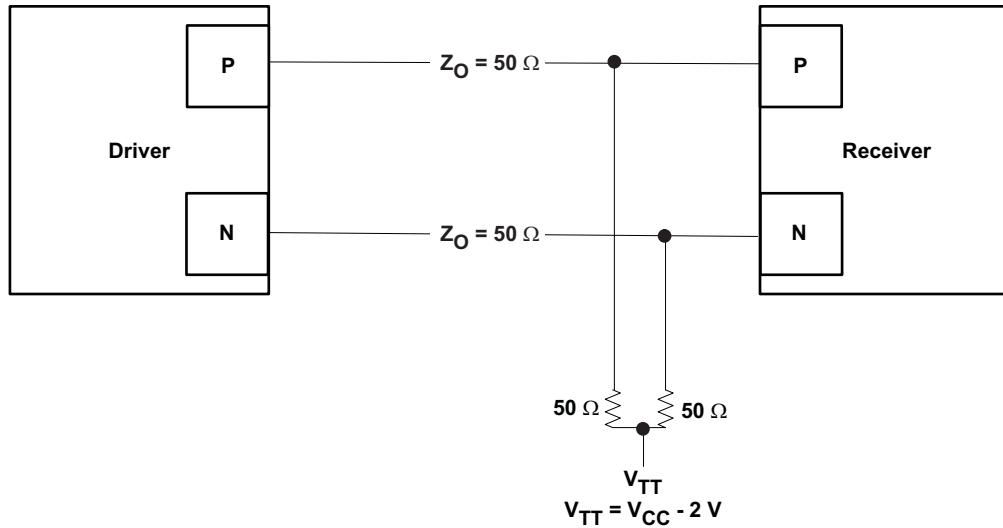


Figure 1. Termination for Output Driver

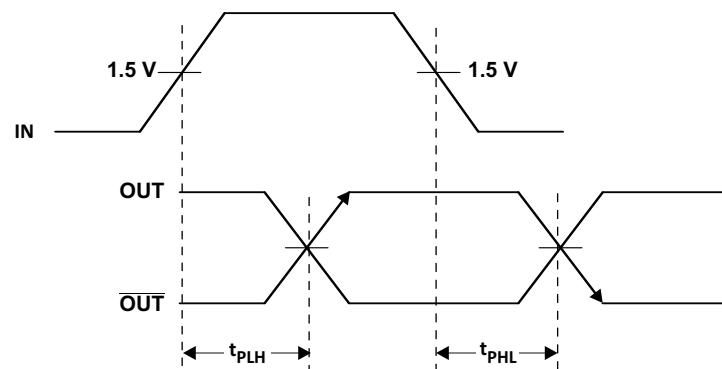


Figure 2. Output Propagation Delay

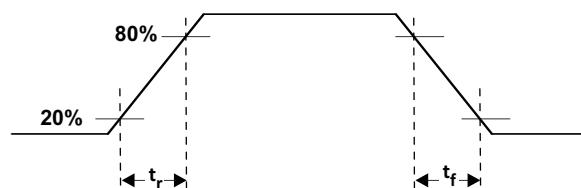


Figure 3. Output Rise and Fall Times

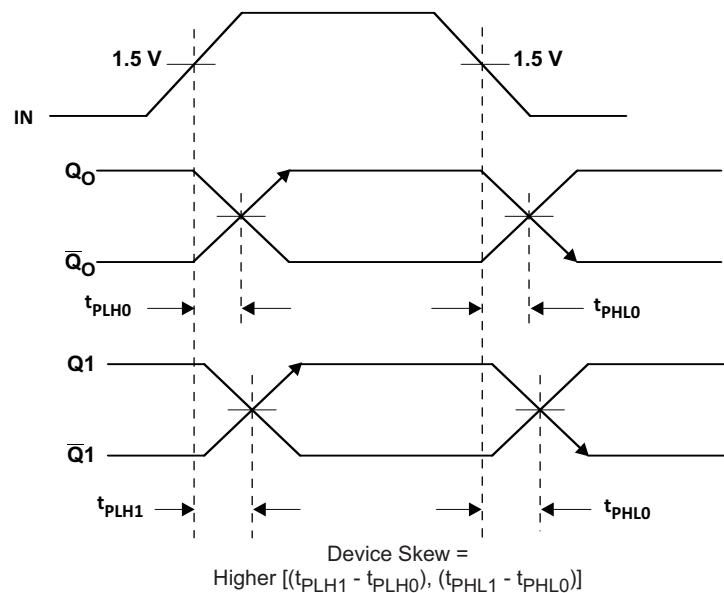


Figure 4. Device Skew

7.9 Typical Characteristics

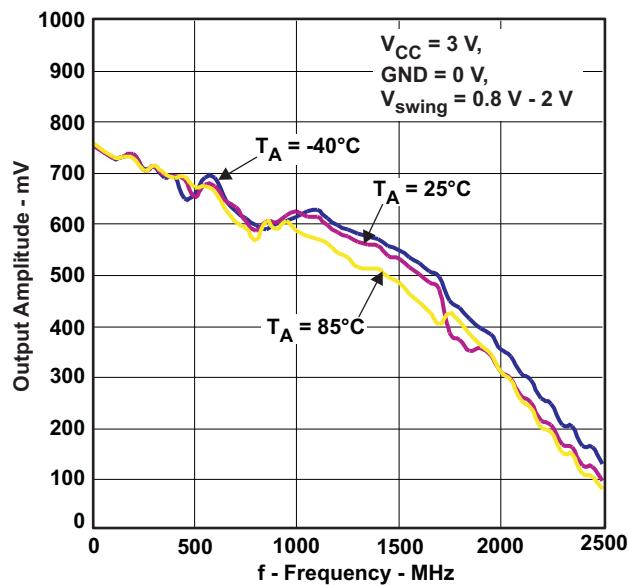


Figure 5. Output Amplitude versus Frequency

8 Device and Documentation Support

8.1 Trademarks

All trademarks are the property of their respective owners.

8.2 Electrostatic Discharge Caution



These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

8.3 Glossary

[SLYZ022](#) — *TI Glossary*.

This glossary lists and explains terms, acronyms, and definitions.

9 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

PACKAGING INFORMATION

Orderable part number	Status (1)	Material type (2)	Package Pins	Package qty Carrier	RoHS (3)	Lead finish/ Ball material (4)	MSL rating/ Peak reflow (5)	Op temp (°C)	Part marking (6)
SN65EPT22D	Active	Production	SOIC (D) 8	75 TUBE	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	EPT22
SN65EPT22D.B	Active	Production	SOIC (D) 8	75 TUBE	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	EPT22
SN65EPT22DGK	Active	Production	VSSOP (DGK) 8	80 TUBE	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	SIQI
SN65EPT22DGK.B	Active	Production	VSSOP (DGK) 8	80 TUBE	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	SIQI
SN65EPT22DGKR	Active	Production	VSSOP (DGK) 8	2500 LARGE T&R	Yes	Call TI Nipdau	Level-1-260C-UNLIM	-40 to 85	SIQI
SN65EPT22DGKR.B	Active	Production	VSSOP (DGK) 8	2500 LARGE T&R	Yes	Call TI	Level-1-260C-UNLIM	-40 to 85	SIQI
SN65EPT22DGKRG4	Active	Production	VSSOP (DGK) 8	2500 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	SIQI
SN65EPT22DGKRG4.B	Active	Production	VSSOP (DGK) 8	2500 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	SIQI
SN65EPT22DR	Active	Production	SOIC (D) 8	2500 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	EPT22
SN65EPT22DR.B	Active	Production	SOIC (D) 8	2500 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	EPT22

⁽¹⁾ **Status:** For more details on status, see our [product life cycle](#).

⁽²⁾ **Material type:** When designated, preproduction parts are prototypes/experimental devices, and are not yet approved or released for full production. Testing and final process, including without limitation quality assurance, reliability performance testing, and/or process qualification, may not yet be complete, and this item is subject to further changes or possible discontinuation. If available for ordering, purchases will be subject to an additional waiver at checkout, and are intended for early internal evaluation purposes only. These items are sold without warranties of any kind.

⁽³⁾ **RoHS values:** Yes, No, RoHS Exempt. See the [TI RoHS Statement](#) for additional information and value definition.

⁽⁴⁾ **Lead finish/Ball material:** Parts may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

⁽⁵⁾ **MSL rating/Peak reflow:** The moisture sensitivity level ratings and peak solder (reflow) temperatures. In the event that a part has multiple moisture sensitivity ratings, only the lowest level per JEDEC standards is shown. Refer to the shipping label for the actual reflow temperature that will be used to mount the part to the printed circuit board.

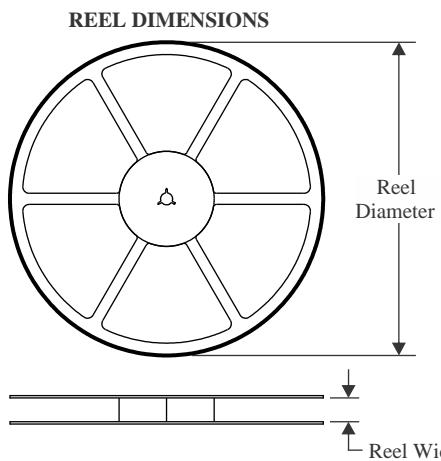
⁽⁶⁾ **Part marking:** There may be an additional marking, which relates to the logo, the lot trace code information, or the environmental category of the part.

Multiple part markings will be inside parentheses. Only one part marking contained in parentheses and separated by a "~" will appear on a part. If a line is indented then it is a continuation of the previous line and the two combined represent the entire part marking for that device.

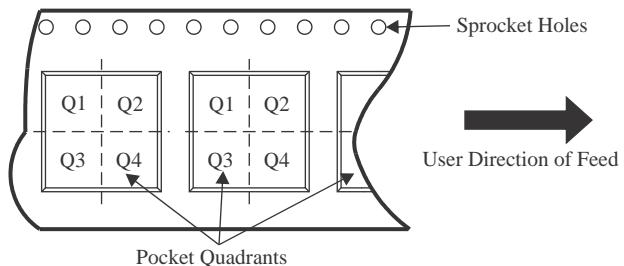
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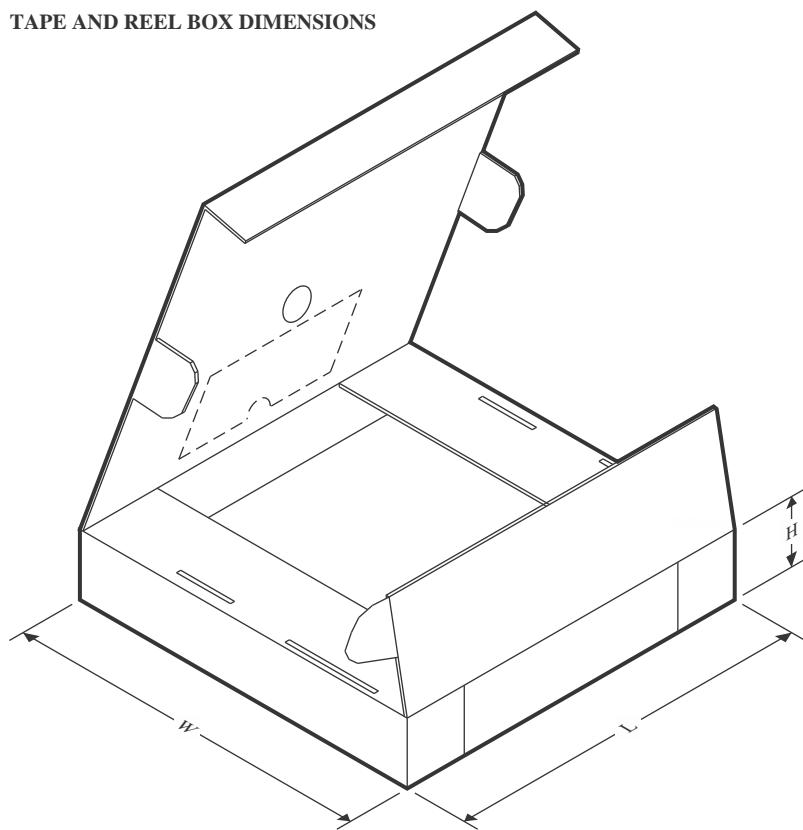
TAPE AND REEL INFORMATION


A0	Dimension designed to accommodate the component width
B0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE


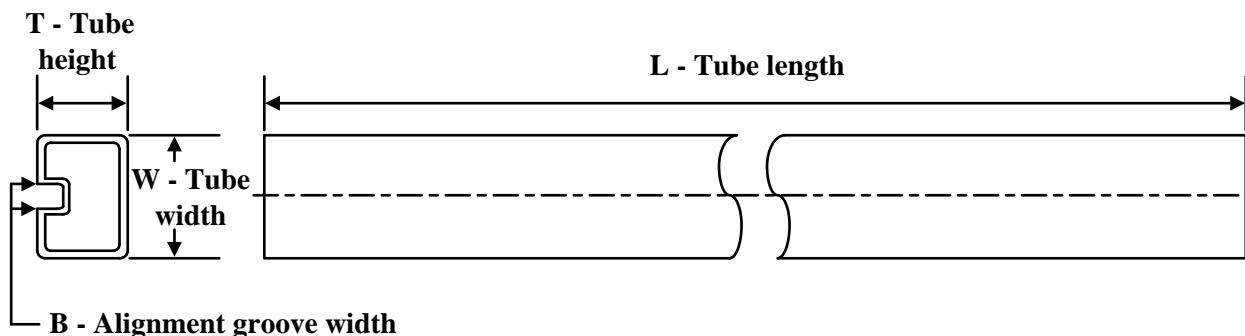
*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
SN65EPT22DGKR	VSSOP	DGK	8	2500	330.0	12.4	5.3	3.4	1.4	8.0	12.0	Q1
SN65EPT22DGKRG4	VSSOP	DGK	8	2500	330.0	12.4	5.3	3.4	1.4	8.0	12.0	Q1
SN65EPT22DR	SOIC	D	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1

TAPE AND REEL BOX DIMENSIONS


*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
SN65EPT22DGKR	VSSOP	DGK	8	2500	353.0	353.0	32.0
SN65EPT22DGKRG4	VSSOP	DGK	8	2500	353.0	353.0	32.0
SN65EPT22DR	SOIC	D	8	2500	353.0	353.0	32.0

TUBE


*All dimensions are nominal

Device	Package Name	Package Type	Pins	SPQ	L (mm)	W (mm)	T (μ m)	B (mm)
SN65EPT22D	D	SOIC	8	75	506.6	8	3940	4.32
SN65EPT22D.B	D	SOIC	8	75	506.6	8	3940	4.32
SN65EPT22DGK	DGK	VSSOP	8	80	330.2	6.6	3005	1.88
SN65EPT22DGK.B	DGK	VSSOP	8	80	330.2	6.6	3005	1.88

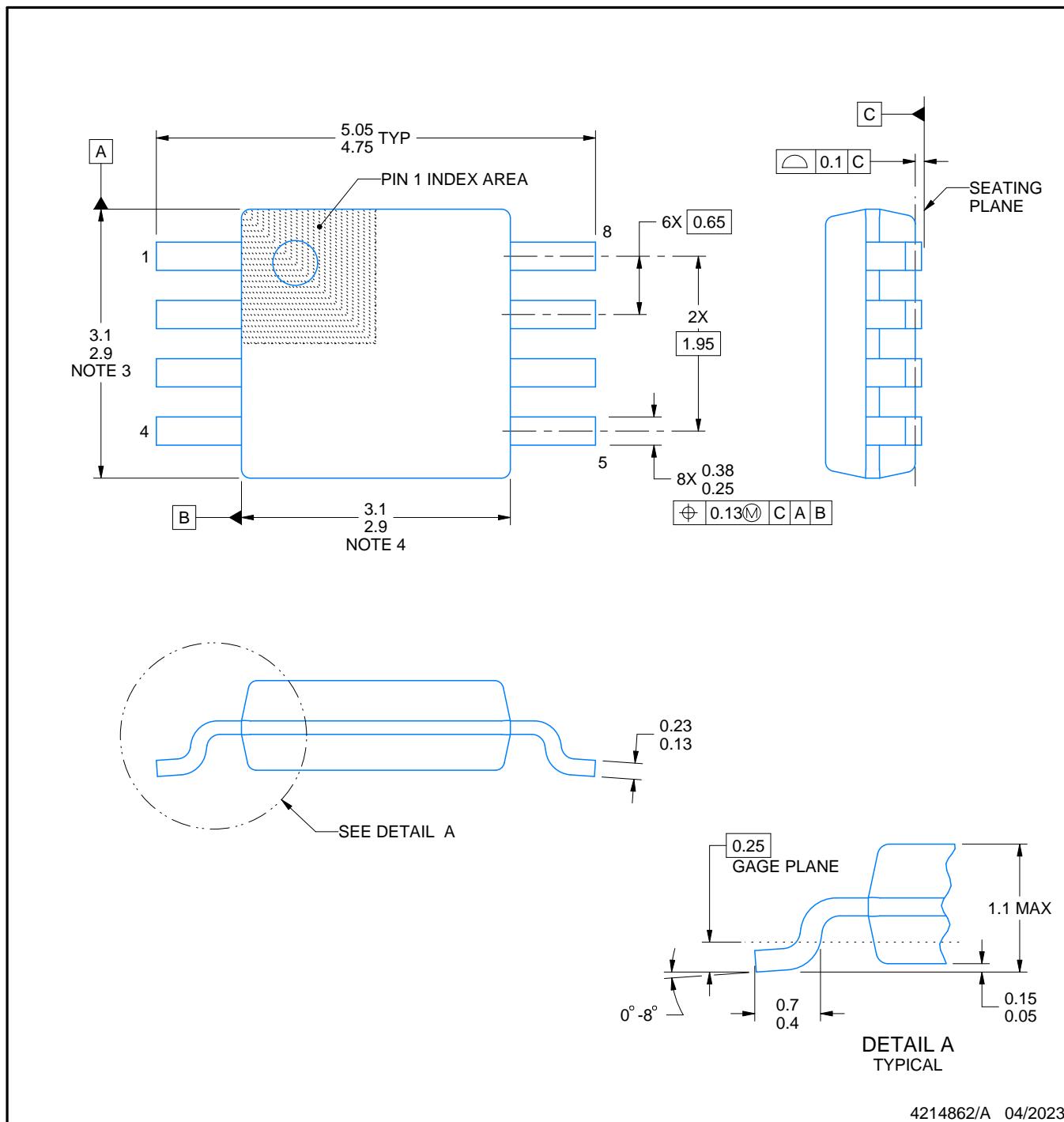
PACKAGE OUTLINE

DGK0008A



VSSOP - 1.1 mm max height

SMALL OUTLINE PACKAGE



NOTES:

PowerPAD is a trademark of Texas Instruments.

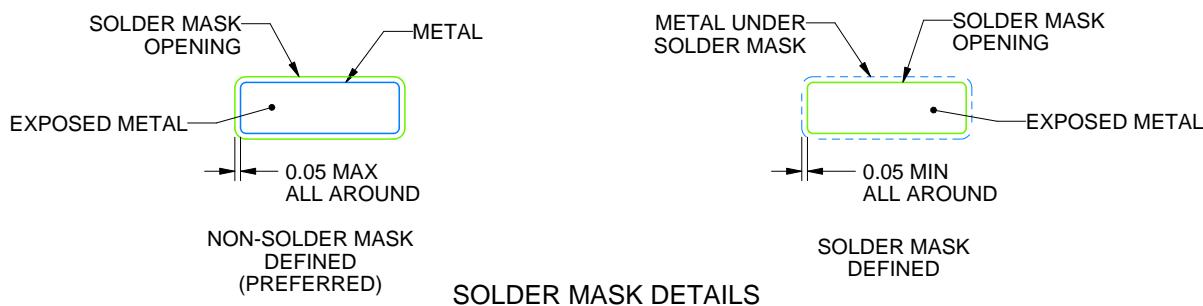
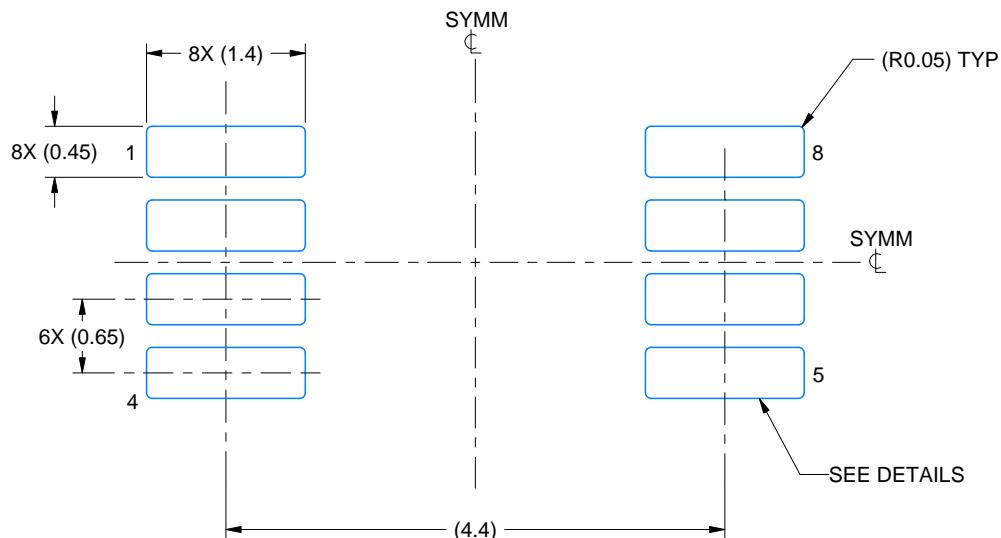
1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.15 mm per side.
4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.25 mm per side.
5. Reference JEDEC registration MO-187.

EXAMPLE BOARD LAYOUT

DGK0008A

™ VSSOP - 1.1 mm max height

SMALL OUTLINE PACKAGE



4214862/A 04/2023

NOTES: (continued)

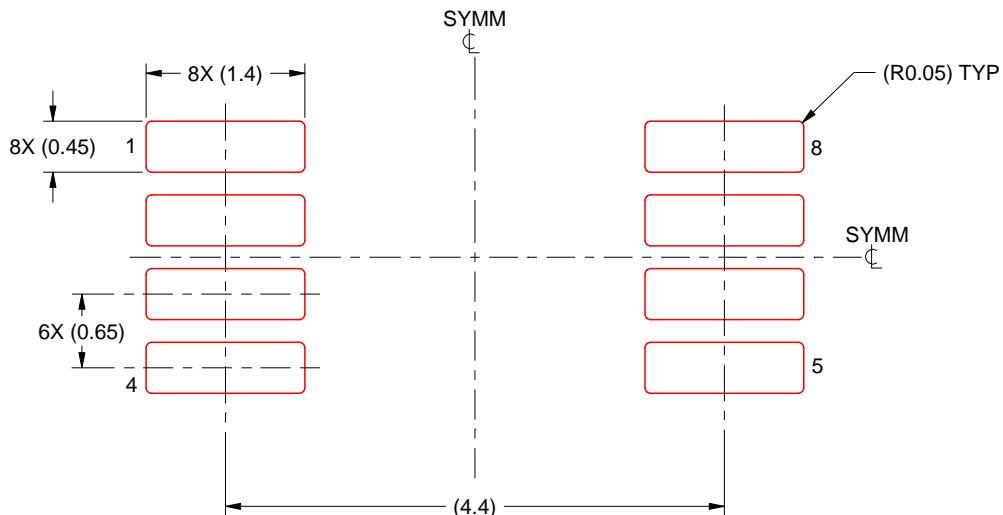
6. Publication IPC-7351 may have alternate designs.
7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.
8. Vias are optional depending on application, refer to device data sheet. If any vias are implemented, refer to their locations shown on this view. It is recommended that vias under paste be filled, plugged or tented.
9. Size of metal pad may vary due to creepage requirement.

EXAMPLE STENCIL DESIGN

DGK0008A

TM VSSOP - 1.1 mm max height

SMALL OUTLINE PACKAGE



SOLDER PASTE EXAMPLE
SCALE: 15X

4214862/A 04/2023

NOTES: (continued)

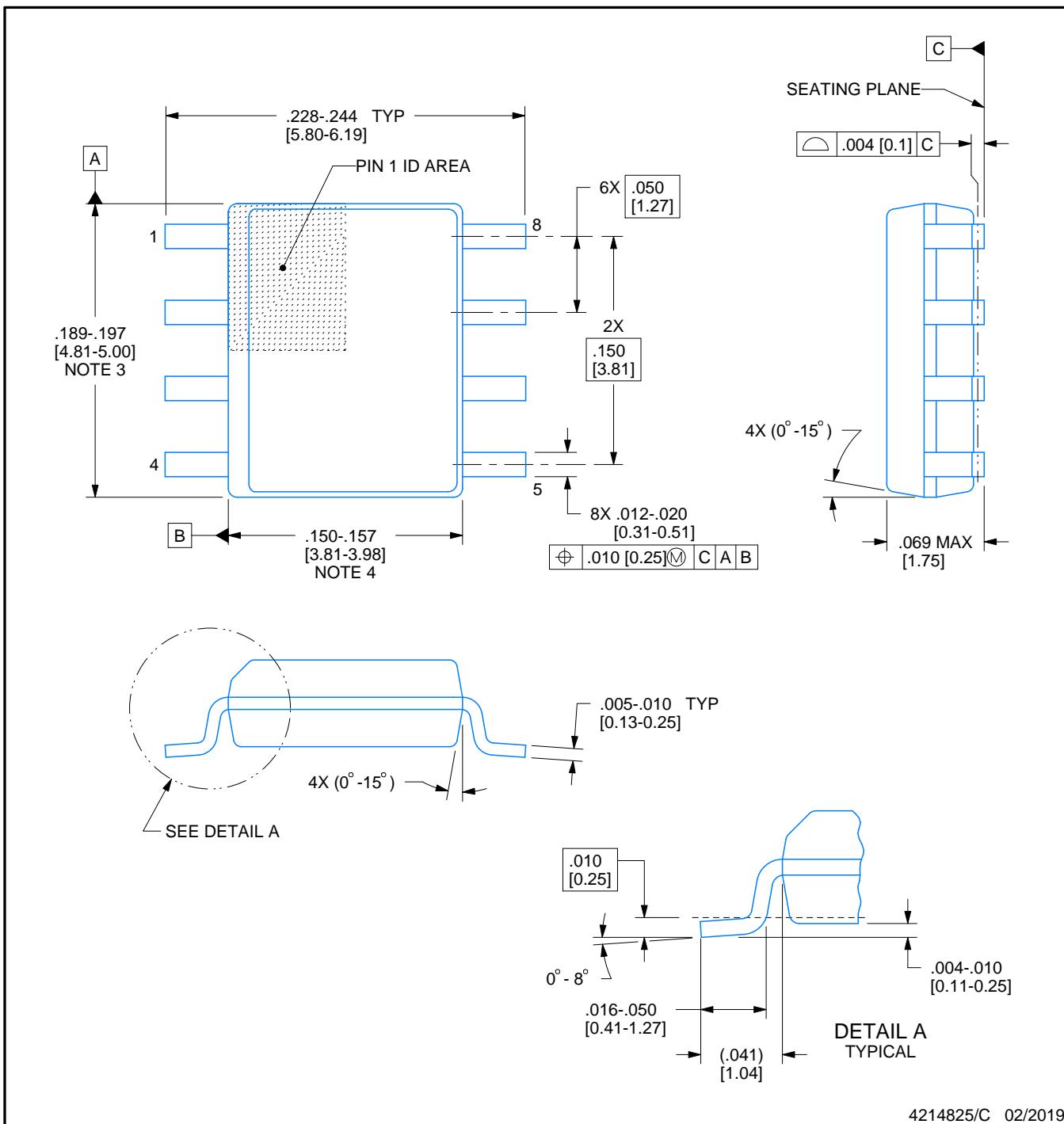
11. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
12. Board assembly site may have different recommendations for stencil design.



PACKAGE OUTLINE

SOIC - 1.75 mm max height

SMALL OUTLINE INTEGRATED CIRCUIT



NOTES:

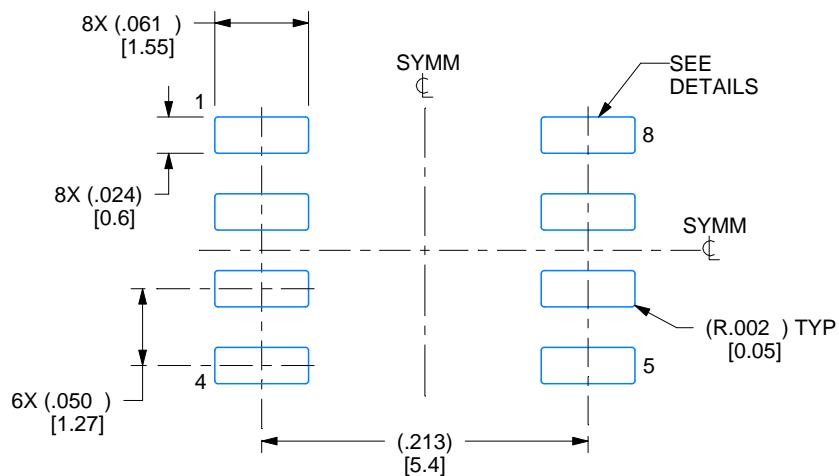
1. Linear dimensions are in inches [millimeters]. Dimensions in parenthesis are for reference only. Controlling dimensions are in inches. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed .006 [0.15] per side.
4. This dimension does not include interlead flash.
5. Reference JEDEC registration MS-012, variation AA.

EXAMPLE BOARD LAYOUT

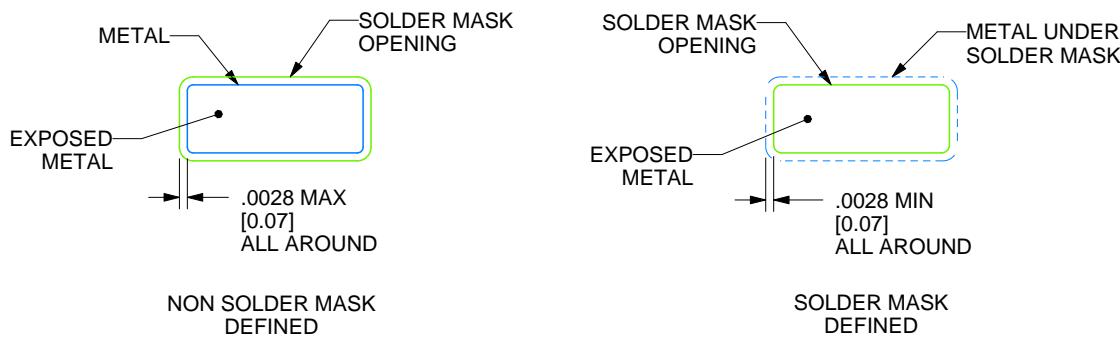
D0008A

SOIC - 1.75 mm max height

SMALL OUTLINE INTEGRATED CIRCUIT



LAND PATTERN EXAMPLE
EXPOSED METAL SHOWN
SCALE:8X



SOLDER MASK DETAILS

4214825/C 02/2019

NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

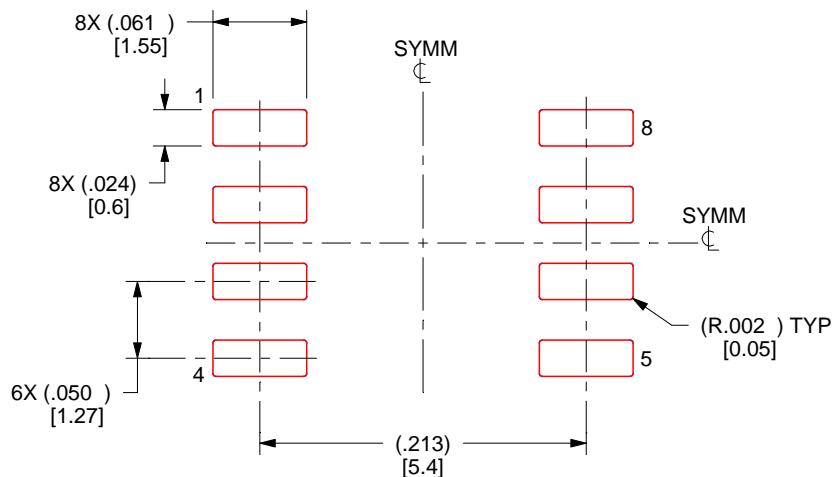
7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.

EXAMPLE STENCIL DESIGN

D0008A

SOIC - 1.75 mm max height

SMALL OUTLINE INTEGRATED CIRCUIT



SOLDER PASTE EXAMPLE
BASED ON .005 INCH [0.125 MM] THICK STENCIL
SCALE:8X

4214825/C 02/2019

NOTES: (continued)

8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
9. Board assembly site may have different recommendations for stencil design.

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